

40V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _C = +25°C
	20mΩ @ V _{GS} = 10V	21.2A
40V	25mΩ @ V _{GS} = 4.5V	19.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Wireless Charging
- DC-DC Converters
- Power Management

Features and Benefits

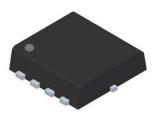
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses Are Minimized
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

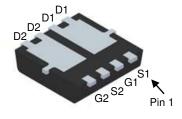
Mechanical Data

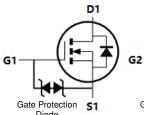
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.072 grams (Approximate)

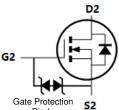
PowerDI3333-8 (Type UXC)











Top View

Bottom View

Internal Schematic

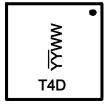
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT4015LDV-7	PowerDI3333-8 (Type UXC)	2,000/Tape & Reel
DMT4015LDV-13	PowerDI3333-8 (Type UXC)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V		
Gate-Source Voltage			Vgss	±16	V
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$			I _D	21.2 17.0	А
Continuous Drain Current (Note 6) V _{GS} = 10V Steady State T _A = +			l _D	7.8 6.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	50	Α		
Maximum Continuous Body Diode Forward Current (Note 6)			Is	2	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			lsм	50	Α
Avalanche Current, L = 0.1mH			las	20.7	Α
Avalanche Energy, L = 0.1mH			Eas	21.4	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.1	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		RθJA	110.6	°C/W
Total Power Dissipation (Note 6) T _A = +25°C		PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		RθJA	61.2	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _θ JC	8.3	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	lgss	_	_	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	•					•	
Gate Threshold Voltage	V _{GS(TH)}	0.75	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Dagger	-	15.3	20	mΩ	$V_{GS} = 10V, I_D = 8A$	
Static Drain-Source On-Nesistance	RDS(ON)	_	20.1	25	11122	$V_{GS} = 4.5V, I_{D} = 4A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)	•						
Input Capacitance	Ciss		808	_	pF	V 20V V 2V	
Output Capacitance	Coss	-	279	_	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	30	_	pF	71 = 1101112	
Gate Resistance	Rg	_	1.4	_	Ω V _{DS} = 0V, V _{GS} = 0V, f = 1MH		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.6	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	15.7	_	nC	V 20V I- 10A	
Gate-Source Charge	Qgs	_	2.9	_	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Qgd	_	3.4	_	nC		
Turn-On Delay Time	tD(ON)	_	7.5	_	ns		
Turn-On Rise Time	tR	_	2.7	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 6\Omega, I_D = 10A$	
Turn-Off Delay Time	tD(OFF)	_	17.4	_	ns		
Turn-Off Fall Time	t _F	_	8.9	_	ns		
Body Diode Reverse Recovery Time	trr	_	26.7	_			
Body Diode Reverse Recovery Charge	QRR	_	16.2	_	nC	$I_F = 10A$, di/dt = $100A/\mu s$	

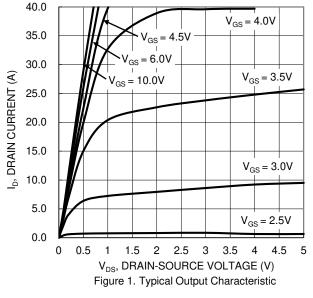
5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided. Notes:

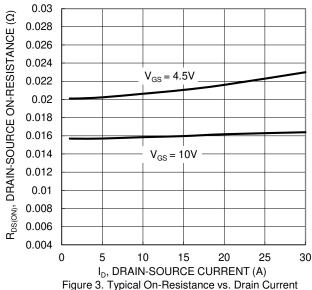
6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.







and Gate Voltage

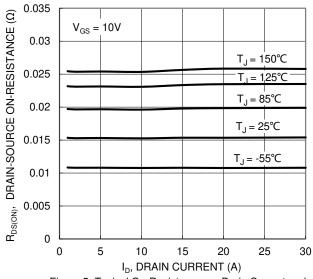


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

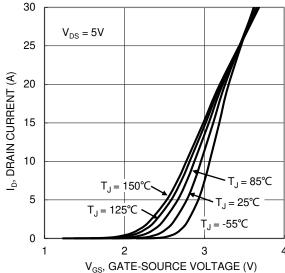
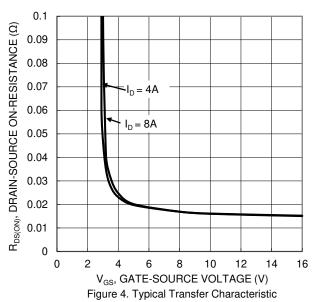


Figure 2. Typical Transfer Characteristic



1.8 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) $V_{GS} = 10V, I_{D} = 8A$ 1.6 1.4 1.2 $V_{GS} = 4.5V, I_{D} = 4A$ 1 0.8 0.6 -50 -25 25 50 75 100 125 150 T., JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



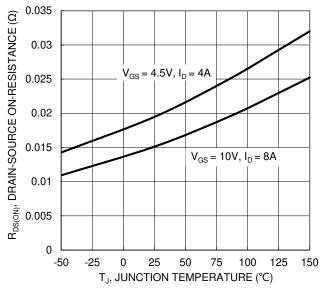


Figure 7. On-Resistance Variation with Temperature

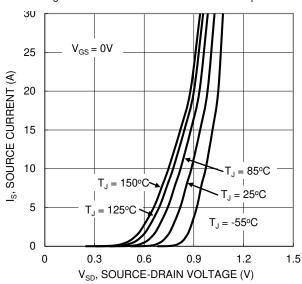
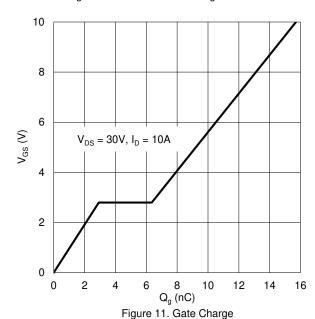
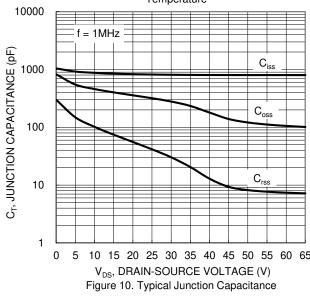


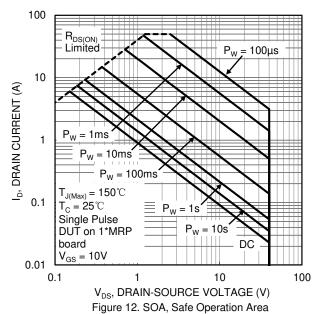
Figure 9. Diode Forward Voltage vs. Current



3 $V_{\text{GS}(TH)},$ GATE THRESHOLD VOLTAGE (V) 2.5 2 $I_D = 1mA$ 1.5 $I_D = 250 \mu A$ 1 0.5 0 25 -50 0 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction
Temperature







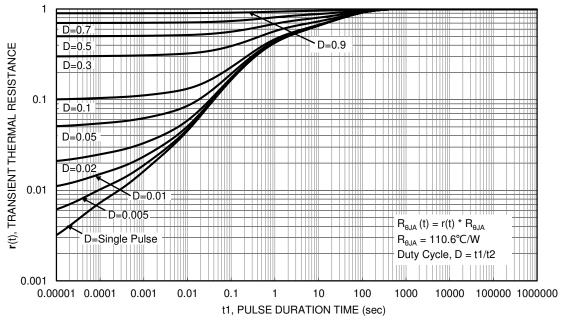


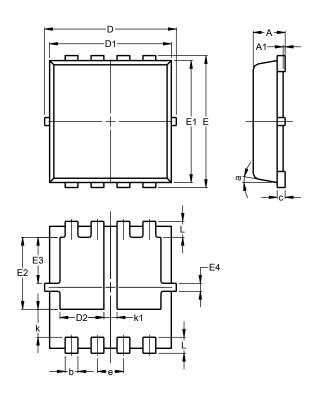
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

PowerDI3333-8 (Type UXC)

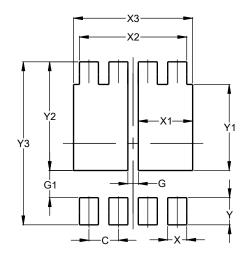


PowerDI3333-8							
(Type UXC)							
Dim	Min Max		Тур				
Α	0.75	0.85	0.80				
A 1	0.00	0.05					
b	0.25	0.40	0.32				
С	0.10	0.25	0.15				
D	3.20	3.40	3.30				
D1	2.95	3.15	3.05				
D2	0.90	1.30	1.10				
Е	3.20	3.40	3.30				
E1	2.95	3.15	3.05				
E2	1.60	2.00	1.80				
E3	0.95	1.35	1.15				
E4	0.10	0.30	0.20				
Ф	-	-	0.65				
L	0.30	0.50	0.40				
k	0.50	0.90	0.70				
k1	0.13	0.53	0.33				
а	0°	12°	10°				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UXC)



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.600			
Х	0.420			
X1	1.200			
X2	2.370			
Х3	2.630			
Υ	0.600			
Y1	1.900			
Y2	2.400			
Y3	3.600			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com